

IGBT Chip in NPT-technology

FEATURES:

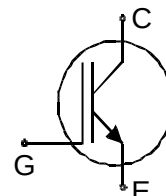
- 600V NPT technology
- 100µm chip
- positive temperature coefficient
- easy paralleling

This chip is used for:

- IGBT Modules

Applications:

- drives



Chip Type	V _{CE}	I _{CN}	Die Size	Package	Ordering Code
SIGC25T60NC	600V	30A	4.5 x 5.71 mm ²	sawn on foil	Q67050-A4143-A001

MECHANICAL PARAMETER:

Raster size	4.5 x 5.71	mm ²
Area total / active	25.69 / 21.4	
Emitter pad size	2x(2.18x1.58)	
Gate pad size	0.68 x 1.08	
Thickness	100	µm
Wafer size	150	mm
Flat position	270	deg
Max.possible chips per wafer	566	
Passivation frontside	Photoimide	
Emitter metallization	3200 nm Al Si 1%	
Collector metallization	1400 nm Ni Ag –system suitable for epoxy and soft solder die bonding	
Die bond	electrically conductive glue or solder	
Wire bond	Al, ≤500µm	
Reject Ink Dot Size	Ø 0.65mm ; max 1.2mm	
Recommended Storage Environment	store in original container, in dry nitrogen, < 6 month at an ambient temperature of 23°C	

MAXIMUM RATINGS:

Parameter	Symbol	Value	Unit
Collector-emitter voltage	V_{CE}	600	V
DC collector current, limited by T_{jmax}	I_C	40	A
Pulsed collector current, t_p limited by T_{jmax}	I_{cpuls}	80	A
Gate emitter voltage	V_{GE}	± 20	V
Operating junction and storage temperature	T_j, T_{stg}	-55 ... +150	°C

STATIC CHARACTERISTICS (tested on chip), $T_j=25^\circ\text{C}$, unless otherwise specified:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Collector-emitter breakdown voltage	$V_{(BR)CES}$	$V_{GE}=0V, I_C=1000\mu A$	600			V
Collector-emitter saturation voltage	$V_{CE(sat)}$	$V_{GE}=15V, I_C=30A$	1.7	2.0	2.5	
Gate-emitter threshold voltage	$V_{GE(th)}$	$I_C=700\mu A, V_{GE}=V_{CE}$	4.5	5.5	6.5	
Zero gate voltage collector current	I_{CES}	$V_{CE}=600V, V_{GE}=0V$			100	μA
Gate-emitter leakage current	I_{GES}	$V_{CE}=0V, V_{GE}=30V$			120	nA

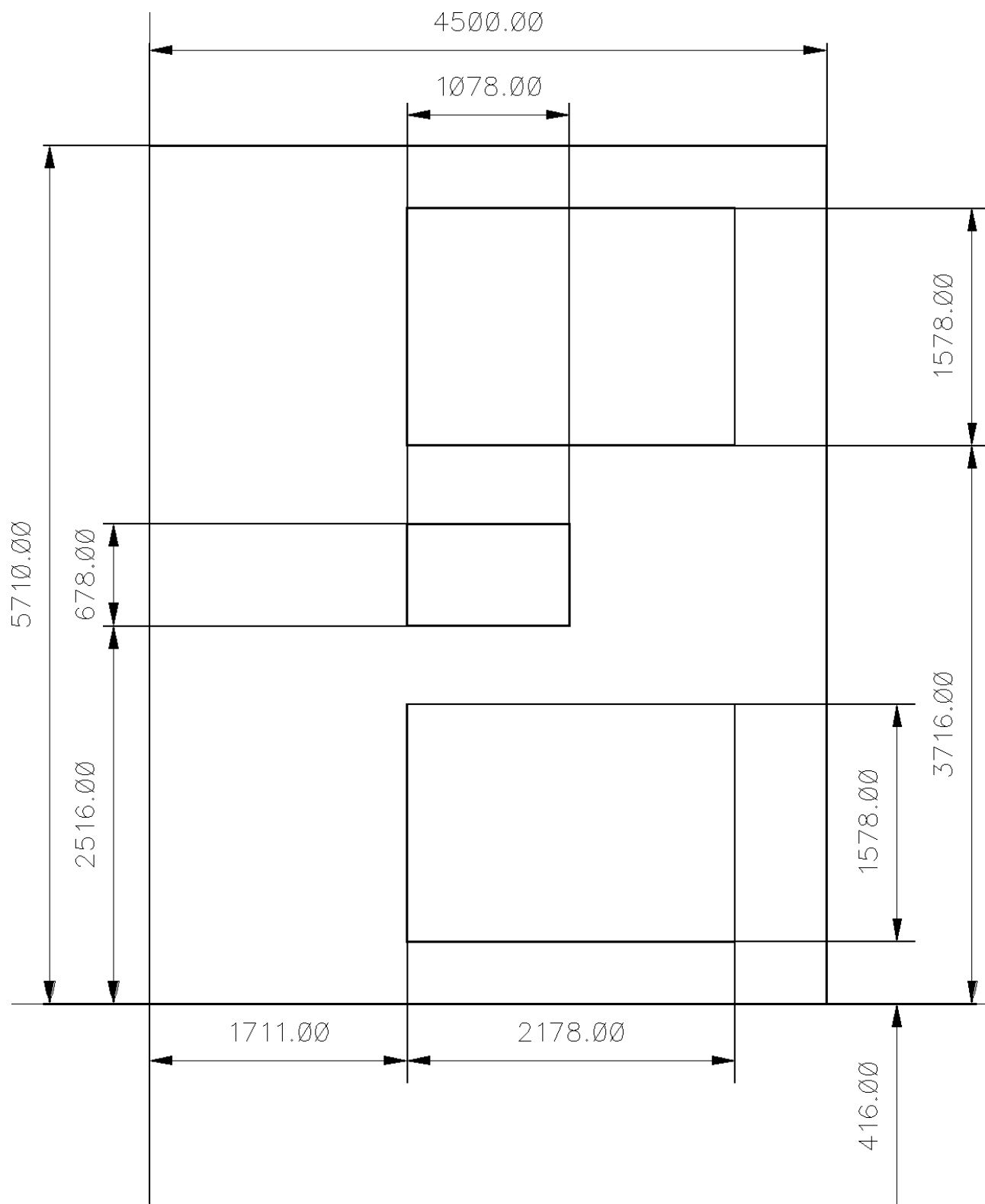
DYNAMIC CHARACTERISTICS (tested at component):

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Input capacitance	C_{iss}	$V_{CE}=25V$	-	1.3		nF
Output capacitance	C_{oss}	$V_{GE}=0V$	-	tbd		
Reverse transfer capacitance	C_{rss}	$f=1MHz$	-	0.1		

SWITCHING CHARACTERISTICS (tested at component), Inductive Load:

Parameter	Symbol	Conditions	Value			Unit
			min.	typ.	max.	
Turn-on delay time	$t_{d(on)}$	$T_j=125^\circ\text{C}$ $V_{CC}=300V$ $I_C=30A$ $V_{GE}=\pm 15V$ $R_G=8.2\Omega$	-	21		ns
Rise time	t_r		-	8		
Turn-off delay time	$t_{d(off)}$		-	110		
Fall time	t_f		-	25		

CHIP DRAWING:



FURTHER ELECTRICAL CHARACTERISTICS:

This chip data sheet refers to the
device data sheet

FS 30 R06 XL4

Description:

AQL 0,65 for visual inspection according to failure catalog

Electrostatic Discharge Sensitive Device according to MIL-STD 883

Test-Normen Villach/Prüffeld

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